

Novel spin-valve memory architecture

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#	ARTICLE	IF	CITATIONS
1	Bit-selective read and write with coincident current scheme in spin-valve/diode MRAM cells. Electronics Letters, 1998, 34, 1754.	1.0	9
2	Integration of spin valves and GaAs diodes in magnetoresistive random access memory cells. Journal of Applied Physics, 1999, 85, 4779-4781.	2.5	6
3	Exchange bias. Journal of Magnetism and Magnetic Materials, 1999, 192, 203-232.	2.3	4,314
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5	Magnetoresistive random access memories: integration issues for novel magnetic devices into memory cells. , 2000, , .		0
6	Thermally activated sweep-rate dependence of magnetic switching field in nanostructured current-perpendicular spin-valves. Journal of Magnetism and Magnetic Materials, 2002, 247, 237-241.	2.3	18
7	Piezoelectric " Ferromagnetic Interface Engineering for Voltage Driven Coercivity Changes. Materials Research Society Symposia Proceedings, 2004, 819, N5.6.1.	0.1	1
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9	Exchange bias in nanostructures. Physics Reports, 2005, 422, 65-117.	25.6	1,722
10	Self-differential detection using laminated magnetic tunnel junctions. Journal of Applied Physics, 2005, 97, 10P502.	2.5	1
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16	Calculation of magnetic properties of nanostructured films by means of the parallel Monte-Carlo. Computer Research and Modeling, 2013, 5, 693-703.	0.3	1
17	High Performance Calculation of Magnetic Properties and Simulation of Nonequilibrium Phenomena in Nanofilms. , 2014, , 95-107.		1
18	Exchange"Interaction"Like Behavior in Ferroelectric Bilayers. Advanced Materials, 2023, 35, .	21.0	3